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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	
				Filing Date	
				First Named Inventor	Marius Orlowski et al.
				Group Art Unit	
(use as many sheets as necessary)				Examiner Name	
Sheet	1	of	1	Attorney Docket Number	SC12928TP

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. [1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	AB	MONFRAY et al., "50nm-Gate All Around (GAA) – Silicon On Nothing (SON) – Devices: A Simple Way to Co-Integration of GAA Transistors Within Bulk MOSFET Process," IEEE 2002 Symposium On VLSI Technology Digest of Technical Papers, pp. 108-109.	
	AC	BORLAND, "Novel Device Structures by Selective Epitaxial Growth (SEG)," IEEE, 4 pgs. (1987).	
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Examiner Signature	Ruben J. Maldonado	Date Considered	09/03/2024

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

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